

1. Record Nr.	UNINA9911006694703321
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Titolo	RF and microwave modeling and measurement techniques for field effect transistors // Jianjun Gao
Pubbl/distr/stampa	Raleigh, NC, : SciTech Pub., c2010
ISBN	1-61353-090-0 1-61344-286-6
Descrizione fisica	1 online resource (351 p.)
Disciplina	621.3815/284
Soggetti	Field-effect transistors - Testing Compound semiconductors - Testing Field-effect transistors - Mathematical models Compound semiconductors - Mathematical models Microwave measurements Radio measurements
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Contents; Preface; Chapter 1 - Introduction; Chapter 2 - Representation of Microwave Two-Port Network; Chapter 3 - Microwave and RF Measurement Techniques; Chapter 4 - FET Small Signal Modeling and ParameterExtraction; Chapter 5 - FET Nonlinear Modeling and ParameterExtraction; Chapter 6 - Microwave Noise Modeling and ParameterExtraction Technique for FETs; Chapter 7 - Artificial Neural Network Modeling Techniquefor FET; References; Index
Sommario/riassunto	This book is an introduction to microwave and RF signal modeling and measurement techniques for field effect transistors. It assumes only a basic course in electronic circuits and prerequisite knowledge for readers to apply the techniques and improve the performance of integrated circuits, reduce design cycles and increase their chance at first time success. The first chapters offer a general overview and discussion of microwave signal and noise matrices, and microwave measurement techniques. The following chapters address modeling techniques for field effect transistors and cover models such

